MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

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SOT-23

Features

- 340 Watts peak pulse power (tp = $8/20\mu s$)
- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Protection two data lines:
- IEC 61000-4-2 $\pm 8kV$ contact $\pm 15kV$ air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 12A (8/20μs)

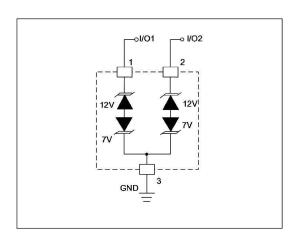
Mechanical Data

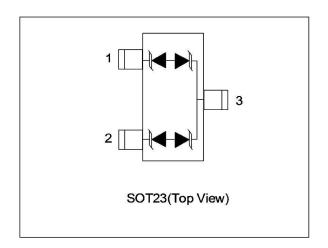
- SOT-23 package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

Applications

- Dataline
- **Automatic Teller Machines**
- Net works
- Power line

Schematic & PIN Configuration





Absolute Maximum Rating

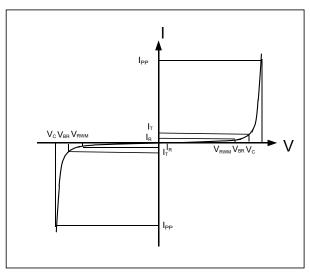
| Rating | Symbol | Value | Units | |
|--|-----------------|----------------|--------------|--|
| Peak Pulse Power (t _p =8/20μs) | P _{PP} | 340 | Watts | |
| Peak Pulse Current (t _p =8/20μs) (note1) | I_{pp} | 12 | A | |
| ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact) | $ m V_{ESD}$ | 15 8 | kV | |
| Lead Soldering Temperature | $T_{ m L}$ | 260(10seconds) | $^{\circ}$ | |
| Junction Temperature | TJ | -55 to + 125 | $^{\circ}$ C | |
| Storage Temperature | $T_{ m stg}$ | -55 to + 125 | $^{\circ}$ C | |

Electrical Characteristics

| | | | Pins 1 to 3 and 2 to 3 (12V TVS) | | Pins 3 to 1 and 3 to 2 (7V TVS) | | | | |
|---------------------------|----------------------|-------------------------|-------------------------------------|---------|------------------------------------|-----|---------|-----|-------|
| Parameter | Symbol | Conditions | Min | Typical | Max | Min | Typical | Max | Units |
| Reverse Stand-Off Voltage | V _{RWM} | | | | 12 | | | 7 | V |
| Reverse Breakdown Voltage | $V_{\scriptsize BR}$ | IT=1mA | 13.3 | | | 7.5 | | | V |
| Reverse Leakage Current | Ir | VR=VRWM | | | 1 | | | 1 | μΑ |
| Clamping Voltage | Vc | IPP=12A,tp=8/20μs | | 28 | | | | | V |
| Clamping Voltage | Vc | IPP=20A,tp=8/20μs | | | | | 20 | | V |
| Junction Capacitance | Cj | $V_R = 0V$, $f = 1MHz$ | | 30 | | | 30 | | pF |

Electrical Parameters (TA = 25°C unless otherwise noted)

| Symbol | Parameter | |
|------------------|--|--|
| IPP | Maximum Reverse Peak Pulse Current | |
| Vc | Clamping Voltage @ Ipp | |
| V _{RWM} | Working Peak Reverse Voltage | |
| Ir | Maximum Reverse Leakage Current @ VRWM | |
| $V_{ m BR}$ | Breakdown Voltage @ IT | |
| Iт | Test Current | |
| | | |
| | | |



Note:. $8/20\mu s$ pulse waveform.





Typical Characteristics

Figure 1: Peak Pulse Power vs. Pulse Time

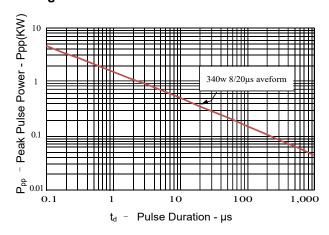


Figure 2: Power Derating Curve

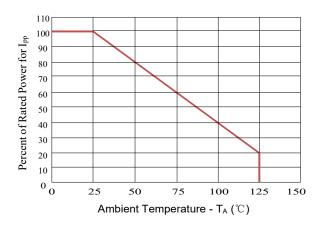


Figure3: Pulse Waveform

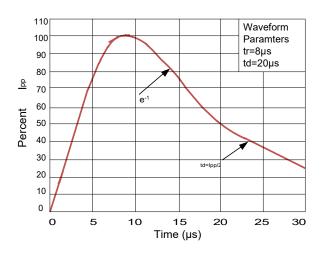
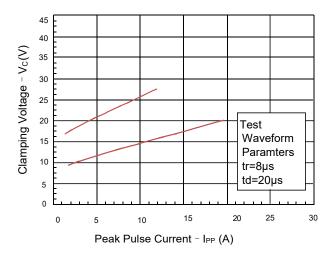
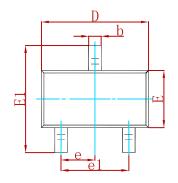


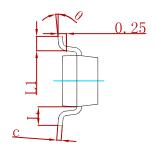
Figure 4: Clamping Voltage vs.lpp

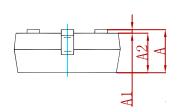






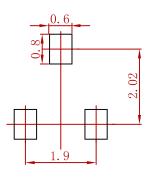






| Symbol | Dimensions | In Millimeters | Dimensions In Inches | | |
|--------|------------|----------------|----------------------|-------|--|
| Symbol | Min | Max | Min | Max | |
| Α | 0.900 | 1.150 | 0.035 | 0.045 | |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 | |
| A2 | 0.900 | 1.050 | 0.035 | 0.041 | |
| b | 0.300 | 0.500 | 0.012 | 0.020 | |
| С | 0.080 | 0.150 | 0.003 | 0.006 | |
| D | 2.800 | 3.000 | 0.110 | 0.118 | |
| Е | 1.200 | 1.400 | 0.047 | 0.055 | |
| E1 | 2.250 | 2.550 | 0.089 | 0.100 | |
| е | 0.950 TYP | | 0.037 TYP | | |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 | |
| L | 0.550 REF | | 0.022 REF | | |
| L1 | 0.300 | 0.500 | 0.012 | 0.020 | |
| θ | 0° | 8° | 0° | 8° | |

Suggested Pad Layout



- 1.Controlling dimension:in millimeters.2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.

REEL SPECIFICATION

| P/N | PKG | QTY |
|-------|--------|------|
| SM712 | SOT-23 | 3000 |



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